Vishay High Power Products

MAP Block Power Module Single Thyristor, 500 A



MAP Block Power

500 A

FEATURES

- Electrically isolated base plate
- 3000 V_{RMS} isolating voltage
- Industrial standard package
- Simplified mechanical designs, rapid assembly
- High surge capability
- Large creepage distances
- Compliant to RoHS directive 2002/95/EC

APPLICATIONS

- Battery chargers
- Welders
- Power converters
- Alternators

MAJOR RATINGS AND CHARACTERISTICS								
SYMBOL	CHARACTERISTICS	VALUES	UNITS					
V _{DRM} /V _{RRM}		800	V					
1		500	А					
I _{T(AV)}	T _C	76	°C					
I _{TSM}	50 Hz	14 000	٥					
	60 Hz	14 658	A					
l ² t	50 Hz	980	kA ² s					
1-1	60 Hz	894	KA-S					
l²√t		9800	kA²√s					
TJ	Range	- 40 to 130	°C					

ELECTRICAL SPECIFICATIONS

PRODUCT SUMMARY

I_{T(AV)}

VOLTAGE RATINGS									
TYPE NUMBER	V _{RRM} /V _{DRM} , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V _{RSM} /V _{DSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I _{RRM} /I _{DRM} AT 130 °C mA						
VSKS500-08PbF	800	900	80						



VSKS500-08PbF

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PARAMETER	SYMBOL		VALUES	UNITS		
Maximum average on-state current at case temperature	I _{T(AV)}	180° conducti	500 76	A °C		
Maximum RMS on-state current	I _{T(RMS)}	As AC switch			76	C
	II (RMS)	t = 10 ms	Nevoltaga		16 646	-
Maximum peak, one-cycle		t = 8.3 ms	No voltage reapplied		17 430	A kA ² s
on-state, non-repetitive	I _{TSM}	t = 10 ms	100 % V _{BBM}	_	14 000	
surge current		t = 8.3 ms	reapplied	Sine half wave, – initial T _J = T _J maximum	14 658	
		t = 10 ms	No voltage reapplied		1385	
N	l ² t	t = 8.3 ms			1265	
Maximum I ² t for fusing		t = 10 ms	100 % V _{RRM}		894	
		t = 8.3 ms	reapplied		894	
Maximum I ² \sqrt{t} for fusing	l²√t	t = 0.1 ms to 1	applied	1385	kA²√s	
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % x π x	$I_{T(AV)} < I < \pi \times I_{T(AV)}$, T _J maximum	0.6839	N
High level value of threshold voltage	V _{T(TO)2}	$(I > \pi \times I_{T(AV)}),$	0.7598	V		
Low level value on-state slope resistance	r _{t1}	(16.7 % x π x	0.393	mΩ		
High level value on-state slope resistance	r _{t2}	$(I > \pi \times I_{T(AV)}), T_J$ maximum 0.389				
Maximum on-state voltage drop	V _{TM}	T _J = 25 °C, 500 A I _{pk}				V

SWITCHING							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Typical delay time	t _d	Gate current 1 A, dl _g /dt = 1 A/ μ s V _d = 0.67 % V _{DRM} , T _J = 25 °C, l _t = 400 A	1.3	us			
Typical turn-off time	t _q	I_{TM} = 750 A, T _J = T _J maximum, dI/dt = 60 A/μs, V _R = 50 V dV/dt = 20 V/μs, Gate 0 V 100 Ω, t _p = 500 μs	200	μs			

BLOCKING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum critical rate of rise of off-state voltage	dV/dt	$T_{\rm J}$ = $T_{\rm J}$ maximum linear to 67 % rated $V_{\rm DRM}$	500	V/µs				
Maximum peak reverse and off-state leakage current	I _{DRM} , I _{RRM}	$T_J = T_J$ maximum, rated V_{DRM}/V_{RRM} applied	80	mA				
RMS insulation voltage	V _{INS}	50 Hz, circuit to base, all terminal shorted, t = 1 s	3000	V				



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TRIGGERING							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum peak gate power	P _{GM}	$T_J = T_J$ maximum, $t_p \le 5$ ms	10.0	W			
Maximum average gate power	P _{G(AV)}	$T_J = T_J$ maximum, f = 50 Hz, d% = 50	2.0	vv			
Maximum peak positive gate current	I _{GM}	$T_J = T_J$ maximum, $t_p \le 5$ ms	3.0	А			
Maximum required DC gate voltage to trigger	V _{GT}		3	V			
Maximum required DC gate current to trigger	I _{GT}	$T_J = 25 \text{ °C}$ Anode supply: 12 V resistive load	200	mA			
Maximum holding current	Ι _Η		600	ШA			
Maximum peak positive gate voltage			20	V			
Maximum peak negative gate voltage	-V _{GM}	$T_J = T_J$ maximum, $t_p \le 5$ ms	5.0	v			
DC gate voltage not to trigger	V _{GD}	$T_J = T_J$ maximum Maximum gate current/voltage not to trigger is	0.30	V			
DC gate current not to trigger	I _{GD}	the maximum value which will not trigger any unit with rated $V_{\mbox{\scriptsize DRM}}$ anode to cathode applied	10	mA			
Maximum non-repetitive rate of rise of dl/dt dl/dt		Gate drive 20 V, 20 $\Omega,$ $t_r \leq 1~\mu s$ $T_J = T_J$ maximum, anode voltage \leq 80 % $V_{DRM},$ $I_t =$ 400 A	1000	A/µs			

THERMAL AND MECHANICAL SPECIFICATIONS							
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum junction operating and storage temperature range		T _J , T _{Stg}		- 40 to 130	°C		
Maximum thermal resistance, junction to case per junction		R _{thJC}	DC operation 0.08				
Maximum thermal resistance, case to heatsink per module		R _{thCS}	Mounting surface smooth, flat and greased	0.035	K/W		
Mounting	MAP Block to heatsink		A mounting compound is recommended and the torque should be rechecked after a period	6 to 8	Nm		
torque ± 10 % busbar to MAP Block			of 3 h to allow for the spread of the compound. Lubricated threads.	12 to 15	INITI		
Approximate weight				430	g		
Approximate weig	ji it			15.3	oz.		
Case style				MAP Block	Power		

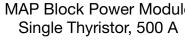
DEVICES	SINUSOIDAL CONDUCTION AT T _J MAXIMUM					RECTANGULAR CONDUCTION AT T _J MAXIMUM					UNITS
	180°	120°	90 °	60°	30 °	180°	120°	90°	60 °	30 °	
VSKS500	0.013	0.0148	0.018	0.026	0.044	0.082	0.0142	0.019	0.027	0.044	K/W

Note

• Table shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

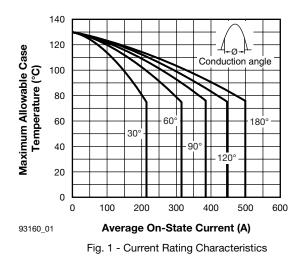
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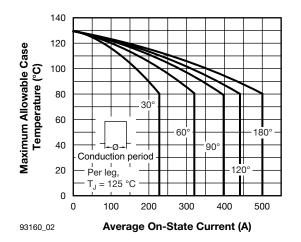
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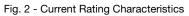


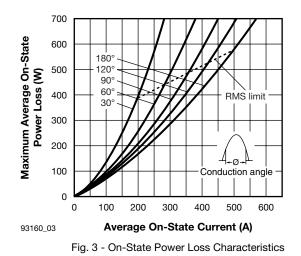
Maximum Average On-State

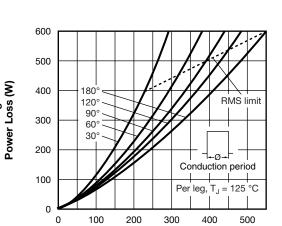
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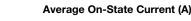
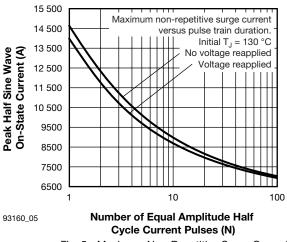
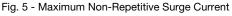


Fig. 4 - On-State Power Loss Characteristics





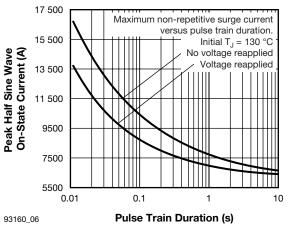


Fig. 6 - Maximum Non-Repetitive Surge Current



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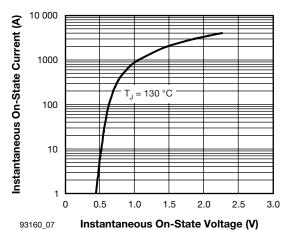


Fig. 7 - On-State Voltage Drop Characteristics

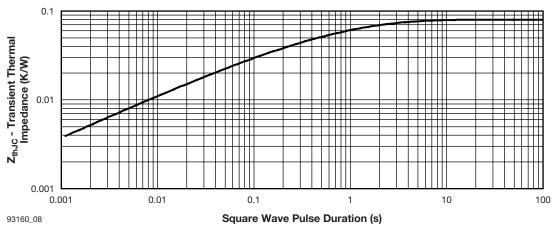
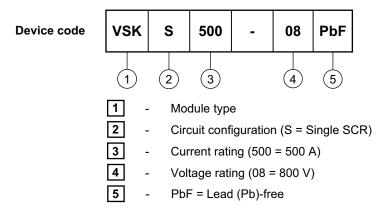


Fig. 8 - Thermal Impedance ZthJC Characteristics

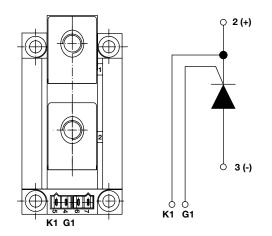
ORDERING INFORMATION TABLE



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CIRCUIT CONFIGURATION



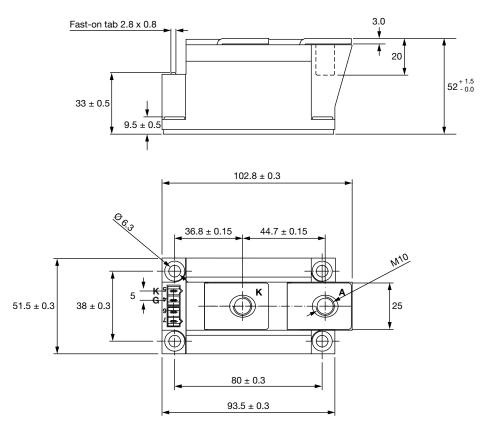
LINKS TO RELATED DOCUMENTS						
Dimensions	www.vishay.com/doc?95379					

Vishay Semiconductors

Thyristor MAP Block

DIMENSIONS in millimeters

SHAY



Notes

- Dimensions are nominal
- · Full engineering drawings are available on request



Vishay

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